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Substitute for form 1449A/PTO			Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/535,358		
			Filing Date			
			First Named Inventor	Andrew R. Barron		
			Group Art Unit			
			Examiner Name			
Sheet	1	of	1	Attorney Docket Number	1789-09405 (21050) CWS	
U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
/TD/	AA	US-6,080,683	06/27/2000			
	AB	US-5,073,408	12/17/1991			
	AC	US-5,132,140	07/21/1992			
	AD	US-5,616,233	04/01/1997			
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/TD/	AH	US-2,505,629	04/25/1950			
FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate) title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issued number(s), publisher, city and/or country where published.				T ²
/TD/	A1	"The Initial Growth Mechanism of Silicon Oxide by Liquid-Phase Deposition", Chou, J.-S. and Lee, S.-C., J. Electrochem. Soc., vol. 140, No. 11, Nov. 1994, pp. 3214-3218.				
	AJ	"A Selective SiO ₂ Film-Formation Technology Using Liquid-Phase Deposition for Fully Planarized Multilevel Interconnections", Hommo, T., Katoh, T., Yamada, Y., and Murao, Y., J. Electrochem. Soc., vol. 140, No. 8, Aug. 1993, pp. 2410-2414.				
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	AL	"Photoassisted Liquid-Phase Deposition of Silicon Dioxide", Huang, C.-T., Chang, P.-H., and Shie, J.-S., J. Electrochem. Soc., vol. 143, No. 6, Jun. 1996, pp. 2044-2048.				
	AM	"A New Process for Silica Coating", Nagayama, H., Honda, H., and Kawahara, H., J. Electrochem. Soc.: Solid State Science and Technology, vol. 135, No. 8, Aug. 1988, pp. 2013-2015.				
/TD/	AN	"Characterization of Silica on Surface Preparation Processes for Advanced Gate Dielectrics", Okorn-Schmidt, H. F., IBM J. Res. Develop., vol. 43, No. 3, May 1999, pp. 351-365.				
Examiner Signature		/Trung Dang/		Dated Considered	08/05/2008	